

Electronic Supplementary Information (ESI) available:

Flux Growth and Characterization of FeSi₄P₄ Single Crystal

Tongtong Yu,^a Shanpeng Wang,^{*ab} Huapeng Ruan,^a Chunlong Li,^a Xixia Zhang,^a Ning Jia,^a Jian Zhang,^{ab} and Xutang Tao^{*ab}

- a. State Key Laboratory of Crystal Materials, Institute of Crystal Materials, Shandong University, No. 27 Shanda South Road, Jinan, 250100, PR China.
- b. State Key Laboratory of Functional Crystal Materials and Device, (Shandong University, Ministry of Education), No. 27 Shanda South Road, Jinan, PR China. E-mail: wshp@sdu.edu.cn, txt@sdu.edu.cn.

Fig. S1 The EDS spectrum of the FSP crystal. No Sn element is detected in the spectrum.

Fig. S2 DSC and TGA data for FSP single crystal. The FSP crystal decomposes at about 1157.1 °C.

Fig. S3 The survey XPS spectrum of the FeSi₄P₄ crystal without being soaked in dilute hydrochloric acid. The Binding Energy of Sn 3d peaks are between 480 eV and 500 eV.

Fig. S4 The M-T curve of the FeSi₄P₄ crystal without being soaked in dilute hydrochloric acid. The value of the magnetization descends to 0 at about 70 K.

Fig. S5 The curve of temperature dependent inverse susceptibility (red point) and the Curie-Weiss fitting (black line).

Table S1 Fractional atomic coordinates and isotropic or equivalent isotropic displacement parameters (Å²).

Table S2 Atomic displacement parameters (Å²).

Table S3 The bond lengths of FeSi₄P₄ crystal.

Table S4 The bond angles of FeSi₄P₄ crystal.

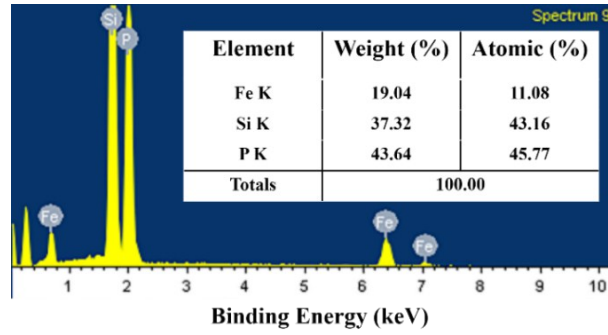


Fig. S1 The EDS spectrum of the FSP crystal. No Sn element is detected in the spectrum.

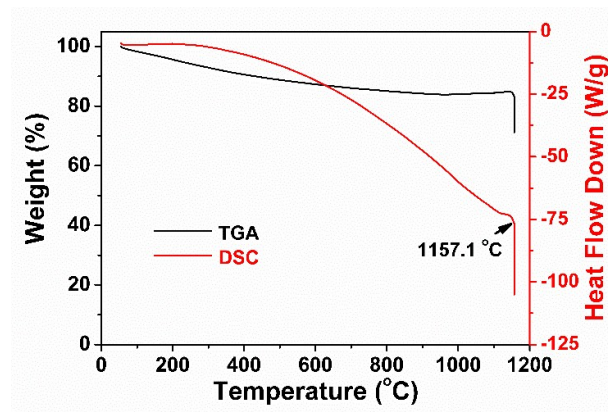


Fig. S2 DSC and TGA data for FSP single crystal. The FSP crystal decomposes at about 1157.1 °C.

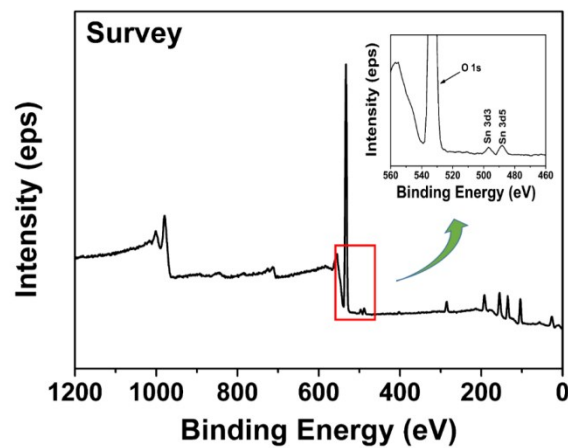


Fig. S3 The survey XPS spectrum of the FeSi_4P_4 crystal without being soaked in dilute hydrochloric acid. The Binding Energy of Sn 3d peaks are between 480 eV and 500 eV.

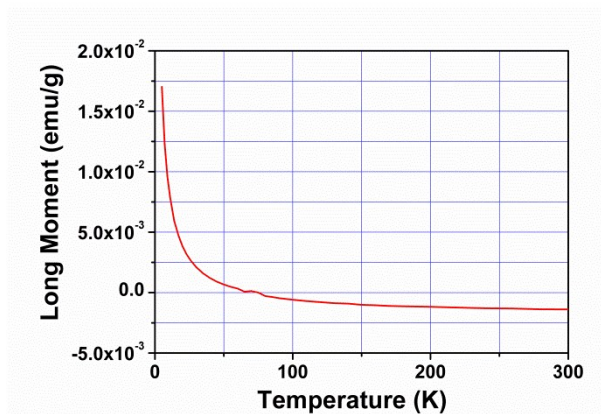


Fig. S4 The M-T curve of the FeSi_4P_4 crystal without being soaked in dilute hydrochloric acid. The value of the magnetization descends to 0 at about 70 K.

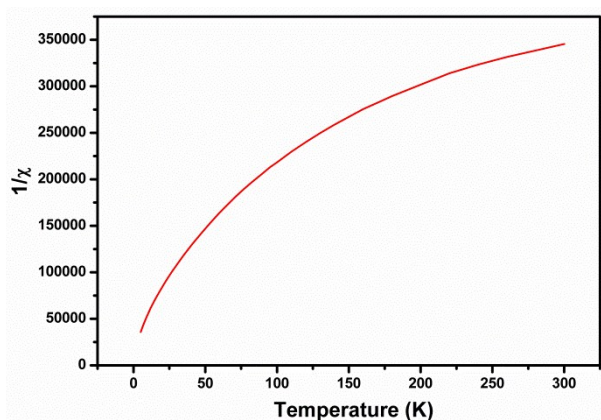


Fig. S5 The curve of temperature dependent inverse susceptibility.

Table S1 Fractional atomic coordinates and isotropic or equivalent isotropic displacement parameters (\AA^2).

	<i>x</i>	<i>y</i>	<i>z</i>	$U_{\text{iso}}^*/U_{\text{eq}}$
Fe1	0.3202 (3)	0.4460 (2)	0.1770 (3)	0.00435 (15)
Si1	0.6668 (4)	0.0441 (3)	0.0611 (3)	0.0063 (4)
Si2	0.5591 (4)	0.7860 (3)	-0.3930 (3)	0.0064 (4)
Si3	0.1652 (4)	0.4189 (3)	-0.1267 (3)	0.0066 (4)
Si4	-0.0031 (4)	0.2240 (3)	0.3952 (3)	0.0063 (4)
P1	0.6484 (4)	0.6666 (3)	-0.0552 (3)	0.0056 (3)
P2	1.0830 (4)	0.0878 (3)	-0.2585 (3)	0.0055 (3)
P3	0.4757 (4)	0.4593 (3)	0.4869 (3)	0.0057 (3)
P4	-0.0453 (3)	0.8470 (3)	0.2934 (3)	0.0059 (3)

Table S2 Atomic displacement parameters (\AA^2).

	U^{11}	U^{22}	U^{33}	U^{12}	U^{13}	U^{23}
Fe1	0.0039 (2)	0.0041 (2)	0.0039 (2)	-0.00086 (17)	-0.00051 (17)	-0.00007 (16)
Si1	0.0066 (8)	0.0055 (8)	0.0060 (8)	-0.0022 (7)	-0.0014 (7)	0.0006 (7)
Si2	0.0060 (8)	0.0037 (8)	0.0067 (9)	0.0003 (6)	-0.0011 (7)	0.0004 (7)
Si3	0.0059 (8)	0.0072 (8)	0.0069 (9)	-0.0013 (7)	-0.0031 (7)	-0.0007 (6)
Si4	0.0063 (8)	0.0082 (9)	0.0045 (8)	-0.0025 (7)	-0.0016 (7)	-0.0006 (7)
P1	0.0054 (8)	0.0028 (7)	0.0069 (8)	-0.0004 (6)	-0.0014 (6)	0.0010 (6)
P2	0.0051 (7)	0.0073 (7)	0.0037 (7)	-0.0022 (6)	-0.0009 (6)	-0.0002 (6)
P3	0.0064 (8)	0.0050 (7)	0.0035 (7)	-0.0017 (6)	0.0005 (6)	0.0003 (6)
P4	0.0059 (8)	0.0048 (7)	0.0060 (8)	-0.0004 (6)	-0.0021 (7)	-0.0004 (6)

Table S3 The bond lengths of FeSi₄P₄ crystal.

Fe1—Si1	2.276 (6)	Si3—P3 ⁱⁱⁱ	2.321 (6)
Fe1—Si3	2.282 (6)	Si4—P3 ^{vi}	2.305 (7)
Fe1—P4	2.301 (6)	Si4—P2 ^{vii}	2.324 (7)
Fe1—Si4	2.302 (5)	Si4—P4 ⁱ	2.336 (7)
Fe1—P3	2.302 (6)	P1—Si1 ^{viii}	2.318 (7)
Fe1—P1	2.336 (5)	P1—Si3 ^{ix}	2.321 (7)
Si1—P2	2.303 (6)	P2—Si2 ⁱⁱ	2.250 (6)
Si1—P1 ⁱ	2.318 (7)	P2—Si3 ^{ix}	2.283 (6)
Si1—P4 ⁱⁱ	2.320 (5)	P2—Si4 ^v	2.324 (7)
Si2—P3 ⁱⁱⁱ	2.231 (6)	P3—Si2 ^x	2.231 (6)
Si2—P2 ^{iv}	2.250 (6)	P3—Si4 ^{ix}	2.305 (7)
Si2—P4 ^v	2.258 (6)	P3—Si3 ^x	2.321 (6)
Si2—P1	2.265 (7)	P4—Si2 ^{vii}	2.258 (6)
Si3—P2 ^{vi}	2.283 (6)	P4—Si1 ^{iv}	2.320 (5)
Si3—P1 ^{vi}	2.321 (7)	P4—Si4 ^{viii}	2.336 (7)

Table S4 The bond angles of FeSi₄P₄ crystal.

Atoms 1,2,3	Angle 1,2,3 [°]	Atoms 1,2,3	Angle 1,2,3 [°]
Si1—Fe1—Si3	87.40 (16)	P1 ^{vi} —Si3—P3 ⁱⁱⁱ	109.82 (14)
Si1—Fe1—P4	177.76 (11)	Fe1—Si4—P3 ^{vi}	112.3 (2)
Si3—Fe1—P4	91.10 (17)	Fe1—Si4—P2 ^{vii}	111.74 (18)

Si1—Fe1—Si4	82.0 (2)	P3 ^{vi} —Si4—P2 ^{vii}	109.29 (14)
Si3—Fe1—Si4	87.7 (2)	Fe1—Si4—P4 ⁱ	129.50 (17)
P4—Fe1—Si4	96.3 (3)	P3 ^{vi} —Si4—P4 ⁱ	94.9 (2)
Si1—Fe1—P3	91.20 (16)	P2 ^{vii} —Si4—P4 ⁱ	96.78 (17)
Si3—Fe1—P3	177.99 (10)	Si2—P1—Si1 ^{viii}	99.84 (17)
P4—Fe1—P3	90.25 (16)	Si2—P1—Si3 ^{ix}	112.46 (14)
Si4—Fe1—P3	90.7 (2)	Si1 ^{viii} —P1—Si3 ^{ix}	97.7 (2)
Si1—Fe1—P1	97.4 (2)	Si2—P1—Fe1	111.36 (18)
Si3—Fe1—P1	90.7 (2)	Si1 ^{viii} —P1—Fe1	125.24 (18)
P4—Fe1—P1	84.3 (2)	Si3 ^{ix} —P1—Fe1	109.4 (2)
Si4—Fe1—P1	178.23 (11)	Si2 ⁱⁱ —P2—Si3 ^{ix}	104.2 (2)
P3—Fe1—P1	91.0 (2)	Si2 ⁱⁱ —P2—Si1	123.94 (18)

Symmetry codes: (i) $x, y-1, z$; (ii) $x+1, y-1, z$; (iii) $x, y, z-1$; (iv) $x-1, y+1, z$; (v) $x+1, y, z-1$; (vi) $x-1, y, z$; (vii) $x-1, y, z+1$; (viii) $x, y+1, z$; (ix) $x+1, y, z$; (x) $x, y, z+1$